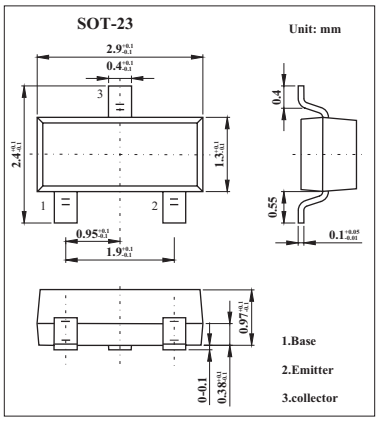
Silicon NPN Epitaxial

2SC3120



■ Features

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■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	30	V
Collector-emitter voltage	V_{CEO}	15	V
Emitter-base voltage	V_{EBO}	3	V
Collector current	I_C	50	mA
Base current	I_B	25	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	125	℃
Storage temperature Range	T_{stg}	-55 to +125	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cut-off current	I_{CBO}	V_{CB} = 30V, I_E = 0			0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB} = 2V, I_C = 0			1.0	μA
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=1mA,I_B=0	15			V
DC current gain	h_{FE}	V_{CE} = 10 V, I_C = 5 mA	40	100	200	
Reverse Transfer Capacitance	Cre	V_{CB}=10V, I_E=0, f=1MHz		0.6	0.9	pF
Transition Frequency	f_T	V_{CE} = 10 V, I_C = 2mA	1500	2400		MHz
Conversion Gain	G_{ce}	V_{CE} = 10 V, I_C = 2mA,f=800MHz	12	17		dB
Noise Figure	NF	F_L=830MHz		8		dB

■ Marking

Marking	HB